



#303 Amst  
M. Branson  
12/6/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

DEC -4 2002

TECHNOLOGY CENTER 2600

In re Appln. Of: YOKOYAMA

Serial No.: 08/992,767

Filed: December 17, 1997

For: CONTACT STRUCTURE IN SEMICONDUCTOR....

Group: 2814

Examiner: DOUGLAS A. WILLE

DOCKET: NEC 19654 CON

BOX RCE

Assistant Commissioner of Patents  
Washington, D.C. 20231

AMENDMENT G WITH RCE

Dear Sir:

This Amendment is being filed in response to the Final Action mailed August 26, 2002.

A Request for Continued Examination (RCE) accompanies this Amendment.

Please amend the Application as follows:

12/03/2002 AMONDAF1 00000104 08992767

01 FC:1202

100.00 CH

8.00 DP

IN THE CLAIMS:

Please amend claims 11 and 20, to read as follows:

11. (Amended) A semiconductor device including both a large-diameter contact hole and a small-diameter contact hole formed to penetrate through an insulator film formed on a semiconductor substrate to reach said semiconductor substrate, each of said large-diameter contact hole and said small-diameter contact hole having a constant-diameter portion formed on a lower portion thereof, and a funnel-shaped portion formed on an upper portion thereof to open or spread upward, said small-diameter contact hole being completely filled with a plug of a refractory conductive material which contacts said semiconductor substrate, and said large-diameter contact hole being partly filled by said refractory conductive material which covers a

12/03/2002 AMONDAF1 00000103 08992767

02 FC:1201

168.00 DP

03 FC:1202

180.00 DP

HAYES SOLOWAY P.C.  
130 W. CUSHING ST.  
TUCSON, AZ 85701  
TEL. 520.882.7623  
FAX. 520.882.7643

175 CANAL STREET  
MANCHESTER, NH 03101  
TEL. 603.668.1400

FAX. 603.668.8567